

## STPS10150C

# High voltage power Schottky rectifier

### Main product characteristics

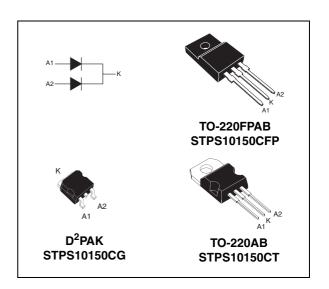
I <sub>F(AV)</sub>	2 x 5 A
V <sub>RRM</sub>	150 V
T <sub>j</sub>	175° C
V <sub>F</sub> (max)	0.75 V

#### Features and benefits

- High junction temperature capability
- Good trade off between leakage current and forward voltage drop
- Low leakage current
- Avalanche capability specified
- Insulated package
  - TO-220FPAB
     Insulating voltage = 2000 V
     Typical package capacitance 12 pF

### **Description**

Dual center tap schottky rectifier designed for high frequency Switched Mode Power Supplies.



#### **Order Codes**

Part Number	Marking
STPS10150CT	STPS10150CT
STPS10150CG	STPS10150CG
STPS10150CG-TR	STPS10150CG
STPS10150CFP	STPS10150CFP

Table 1. Absolute ratings (limiting values)

Symbol	Parameter					Unit	
V <sub>RRM</sub>	Repetitive peak reverse voltage			150	٧		
I <sub>F(RMS)</sub>	RMS forward voltage			10	Α		
I <sub>F(AV)</sub>	Average forward current $\delta = 0.5$	TO-220AB D <sup>2</sup> PAK	T <sub>C</sub> = 155° C	Per diode	5	А	
, ,	0 = 0.5	TO-220FPAB	T <sub>C</sub> = 145° C	Per device	10		
I <sub>FSM</sub>	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$				120	Α	
P <sub>ARM</sub>	Repetitive peak avalanche power $t_p = 1 \mu s T_j = 25^{\circ} C$			3100	W		
T <sub>stg</sub>	Storage temperature range				-65 to + 175	° C	
Tj	Maximum operating junction temperature <sup>(1)</sup>			175	° C		
dV/dt	Critical rate of rise of reverse voltage			10000	V/µs		

<sup>1.</sup>  $\frac{dPtot}{dT_j} < \frac{1}{Rth(j-a)}$  condition to avoid thermal runaway for a diode on its own heatsink

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#### 1 Characteristics

Table 2. Thermal resistance

Symbol		Value	Unit			
		TO-220AB, D <sup>2</sup> PAK	Per diode	4		
ь	th(j-c) Junction to case	TO-220FPAB	rei diode	7	° C/W	
□th(j-c)		TO-220AB, D <sup>2</sup> PAK	Total	2.4		
		TO-220FPAB		5.3	C/VV	
D	R <sub>th(c)</sub> Coupling	TO-220AB, D <sup>2</sup> PAK		0.7		
n <sub>th(c)</sub>		TO-220FPAB	]	3.7		

When the diodes 1 and 2 are used simultaneously:  $\Delta T_{i}(\text{diode 1}) = P(\text{diode 1}) \times R_{th(i-1)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$ 

Table 3. Static electrical characteristics (per diode)

Symbol	Parameter	Tests conditions		Min.	Тур	Max.	Unit
ı_ (1)	Reverse leakage current	T <sub>j</sub> = 25° C	V V			2.0	μΑ
'R`´		T <sub>j</sub> = 125° C	$V_R = V_{RRM}$		0.40	2.0	mA
	Forward voltage drop	T <sub>j</sub> = 25° C	I <sub>F</sub> = 5 A			0.92	
V (2)		T <sub>j</sub> = 125° C			0.69	0.75	V
VF`'		T <sub>j</sub> = 25° C	I <sub>F</sub> = 10 A			1	<b>v</b>
		T <sub>j</sub> = 125° C	I'F = IUA		0.79	0.85	

<sup>1.</sup>  $t_p = 5 \text{ ms}, \delta < 2\%$ 

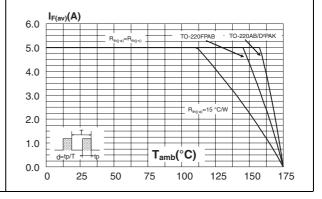
To evaluate the conduction losses use the following equation:

$$P = 0.65 \times I_{F(AV)} + 0.02 I_{F^2(RMS)}$$

Figure 1. Average forward power dissipation versus average forward current (per diode)

 $P_{F(av)}(W)$ 5.0
4.5
4.0
3.5
3.0
2.5
2.0
1.5
1.0
0.5
0.0
0.0
0.5
1.0
1.5
2.0
2.5
3.0
3.5
4.0
4.5
5.0
5.6
6.0

Figure 2. Average forward current versus ambient temperature ( $\delta$  = 0.5, per diode)



<sup>2.</sup>  $t_p = 380 \ \mu s, \ \delta < 2\%$ 

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Figure 3. Normalized avalanche power derating versus pulse duration

Figure 4. Normalized avalanche power derating versus junction temperature

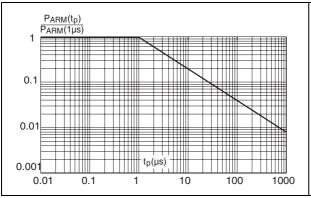
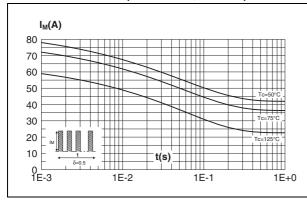


Figure 5. Non repetitive surge peak forward current versus overload duration - maximum values, per diode (TO-220AB, D<sup>2</sup>PAK)

Figure 6. Non repetitive surge peak forward current versus overload duration - maximum values, per diode (TO-220FPAB)



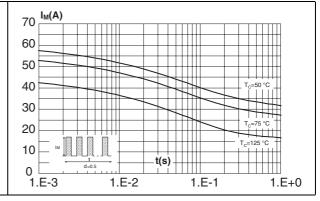
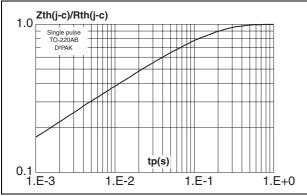
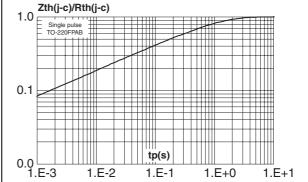


Figure 7. Relative variation of thermal impedance junction to case versus pulse duration (TO-220AB, D<sup>2</sup>PAK)

Figure 8. Relative variation of thermal impedance junction to case versus pulse duration (TO-220FPAB)

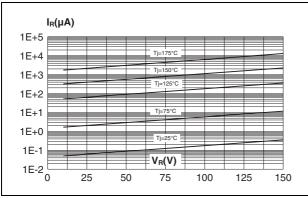




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Figure 9. Reverse leakage current versus reverse voltage applied (typical values, per diode)

Figure 10. Junction capacitance versus reverse voltage applied (typical values, per diode)



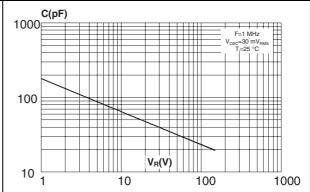
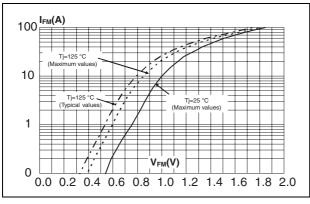


Figure 11. Forward voltage drop versus forward current (per diode)

Figure 12. Thermal resistance, junction to ambient, versus copper surface under tab - Epoxy printed circuit board, e<sub>cu</sub> 35 µm (D<sup>2</sup>PAK only)



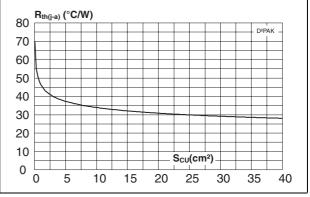
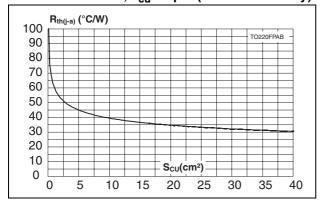


Figure 13. Thermal resistance, junction to ambient, versus copper surface under tab - Epoxy printed circuit board, e<sub>cu</sub> 35 µm (TO220FPAB only)



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STPS10150C Package information

# 2 Package information

Epoxy meets UL94, V0.

Table 4. D<sup>2</sup>PAK Dimensions

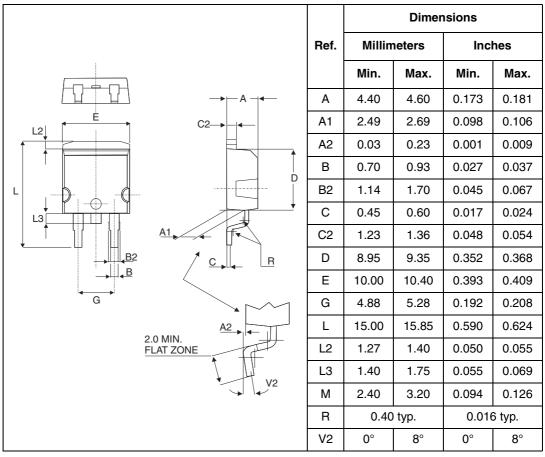
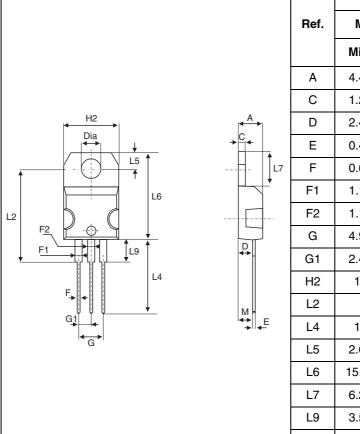


Figure 14. D<sup>2</sup>PAK footprint dimensions (in mm)

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Table 5. TO-220AB Dimensions

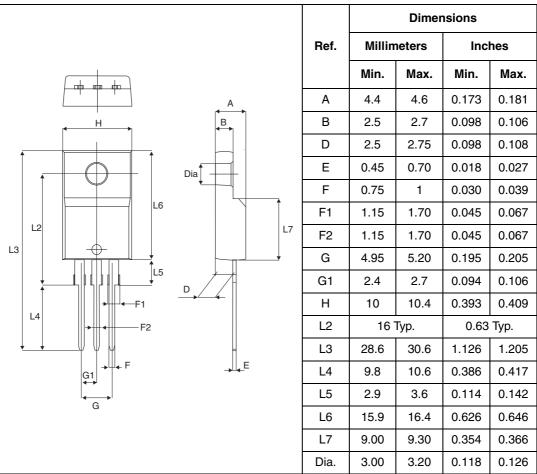


	Dimensions				
Ref.	Millimeters		Inc	hes	
	Min.	Min. Max.		Max.	
Α	4.40	4.60	0.173	0.181	
С	1.23	1.32	0.048	0.051	
D	2.40	2.72	0.094	0.107	
E	0.49	0.70	0.019	0.027	
F	0.61	0.88	0.024	0.034	
F1	1.14	1.70	0.044	0.066	
F2	1.14	1.70	0.044	0.066	
G	4.95	5.15	0.194	0.202	
G1	2.40	2.70	0.094	0.106	
H2	10	10.40	0.393	0.409	
L2	16.4	typ.	0.64	5 typ.	
L4	13	14	0.511	0.551	
L5	2.65	2.95	0.104	0.116	
L6	15.25	15.75	0.600	0.620	
L7	6.20	6.60	0.244	0.259	
L9	3.50	3.93	0.137	0.154	
М	2.6	typ.	0.102	2 typ.	
Diam.	3.75	3.85	0.147	0.151	

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Table 6. TO-220FPAB Dimensions



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Ordering information STPS10150C

# 3 Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS10150CT	STPS10150CT	TO-220AB	2.20 g	50	Tube
STPS10150CG	STPS10150CG	D <sup>2</sup> PAK	1.48 g	50	Tube
STPS10150CG-TR	STPS10150CG	D <sup>2</sup> PAK	1.48 g	1000	Tape and reel
STPS10150CFP	STPS10150CFP	TO-220FPAB	2.0 g	50	Tube

# 4 Revision history

Date	Revision	Description of Changes
Jul-2003	5B	Last update.
19-Jun-2006	6	Reformatted to current standard. Added ECOPACK statement. Added TO220FPAB.

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